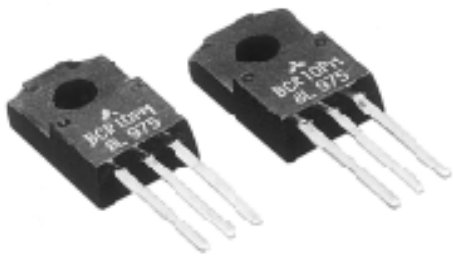


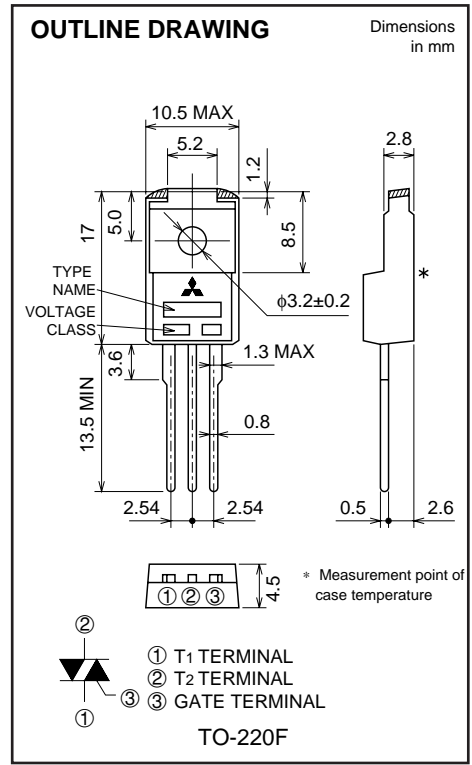
BCR10PM

MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

BCR10PM



- **IT (RMS)** 10A
- **VDRM** 400V/600V
- **IFGT I , IRGT I , IRGT III** 30mA (20mA) *5
- **Viso**..... 1500V
- **UL Recognized: File No. E80276**



APPLICATION

Switching mode power supply, light dimmer, electric flasher unit, hair drier, control of household equipment such as TV sets · stereo · refrigerator · washing machine · infrared kotatsu · carpet, small motor control, copying machine, electric tool, solenoid drivers, other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
VDRM	Repetitive peak off-state voltage*1	400	600	V
VDSM	Non-repetitive peak off-state voltage*1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS)	RMS on-state current	Commercial power frequency, sine full wave 360° conduction, Tc=85°C	10	A
ITSM	Surge on-state current	60Hz sinewave 1 full cycle, peak value, non-repetitive	100	A
I ² t	I ² t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	41.6	A ² s
PGM	Peak gate power dissipation		5	W
PG (AV)	Average gate power dissipation		0.5	W
VGM	Peak gate voltage		10	V
IGM	Peak gate current		2	A
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.0	g
Viso	Isolation voltage	Ta=25°C, AC 1 minute, T1 · T2 · G terminal to case	1500	V

*1. Gate open.

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MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

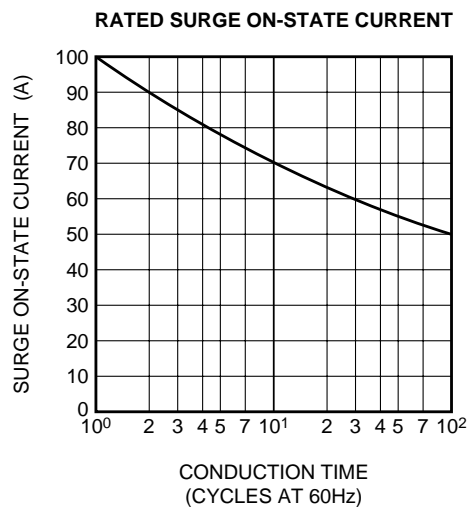
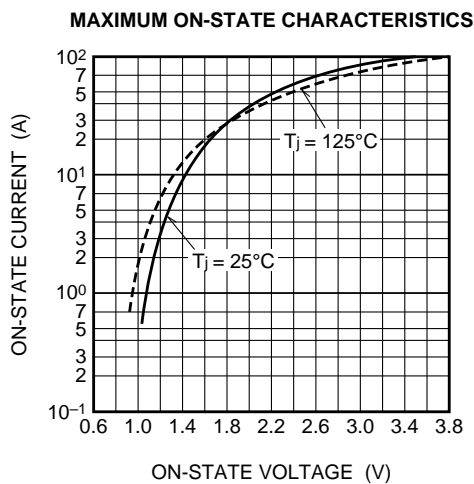
ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit	
			Min.	Typ.	Max.		
IDRM	Repetitive peak off-state current	$T_j=125^\circ\text{C}$, V_{DRM} applied	—	—	2.0	mA	
VTM	On-state voltage	$T_c=25^\circ\text{C}$, $I_{\text{TM}}=15\text{A}$, Instantaneous measurement	—	—	1.5	V	
VFGT I	Gate trigger voltage *2	$T_j=25^\circ\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	I	—	—	1.5	V
VRGT I			II	—	—	1.5	V
VRGT III			III	—	—	1.5	V
IFGT I	Gate trigger current *2	$T_j=25^\circ\text{C}$, $V_D=6\text{V}$, $R_L=6\Omega$, $R_G=330\Omega$	I	—	—	30*5	mA
IRGT I			II	—	—	30*5	mA
IRGT III			III	—	—	30*5	mA
VGD	Gate non-trigger voltage	$T_j=125^\circ\text{C}$, $V_D=1/2V_{\text{DRM}}$	0.2	—	—	V	
$R_{\text{th (j-c)}}$	Thermal resistance	Junction to case *4	—	—	3.5	$^\circ\text{C/W}$	
$(dv/dt)_c$	Critical-rate of rise of off-state commutating voltage		*3	—	—	$\text{V}/\mu\text{s}$	

- *2. Measurement using the gate trigger characteristics measurement circuit.
- *3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.
- *4. The contact thermal resistance $R_{\text{th (c-f)}}$ in case of greasing is 0.5°C/W .
- *5. High sensitivity ($I_{\text{GT}} \leq 20\text{mA}$) is also available. (IGT item ①)

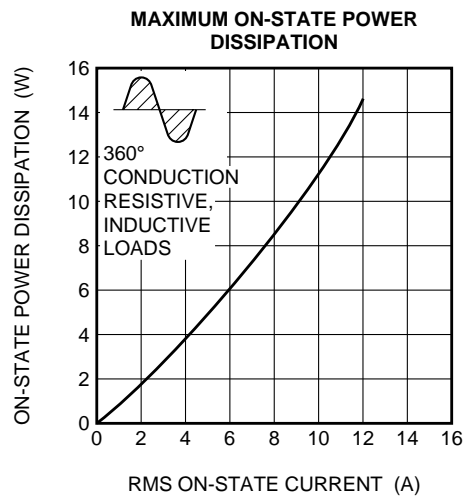
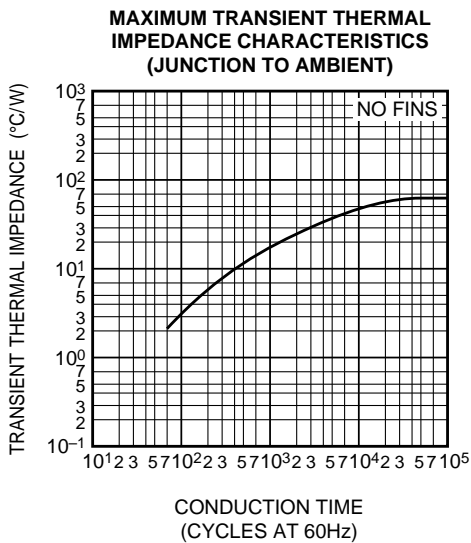
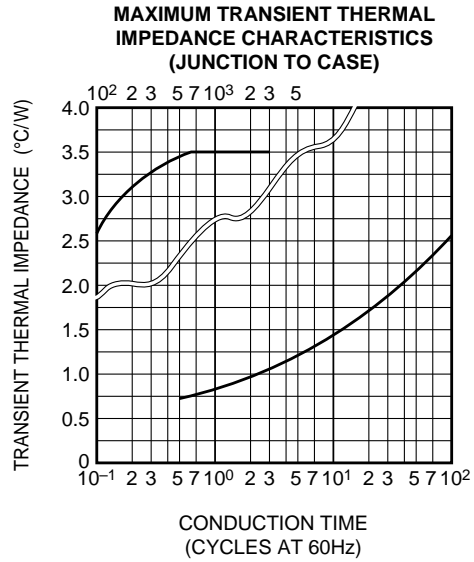
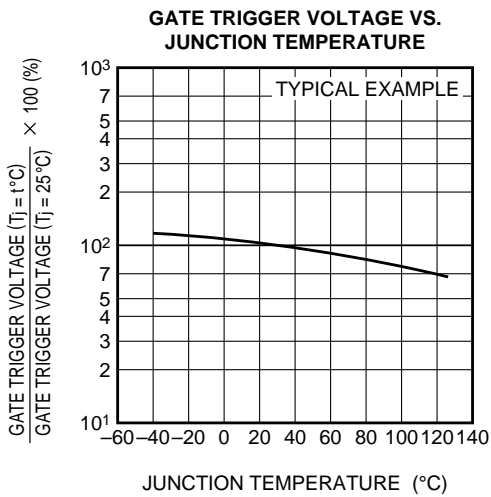
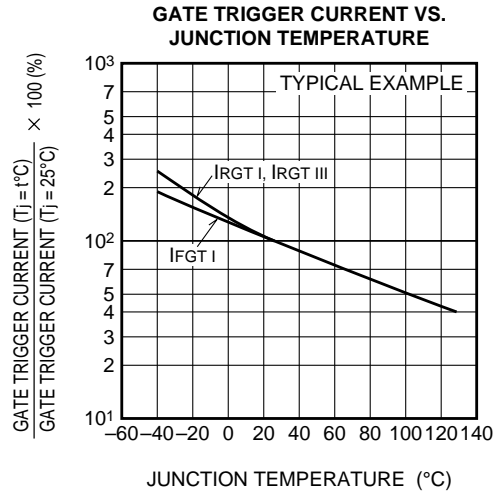
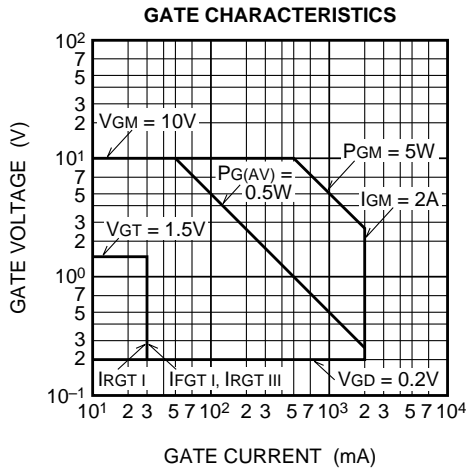
Voltage class	V_{DRM} (V)	$(dv/dt)_c$			Test conditions	Commutating voltage and current waveforms (inductive load)
		Symbol	Min.	Unit		
8	400	R	—	$\text{V}/\mu\text{s}$	1. Junction temperature $T_j=125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -5.0\text{A/ms}$ 3. Peak off-state voltage $V_D=400\text{V}$	
		L	10			
12	600	R	—			
		L	10			

PERFORMANCE CURVES



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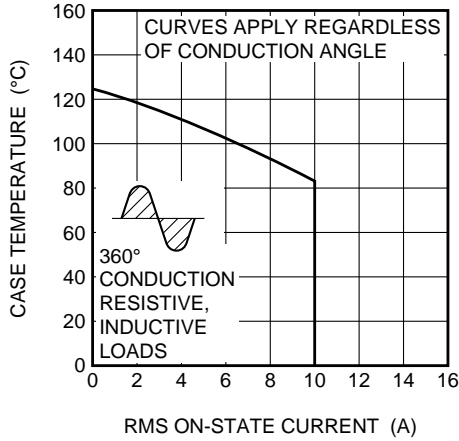
MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE



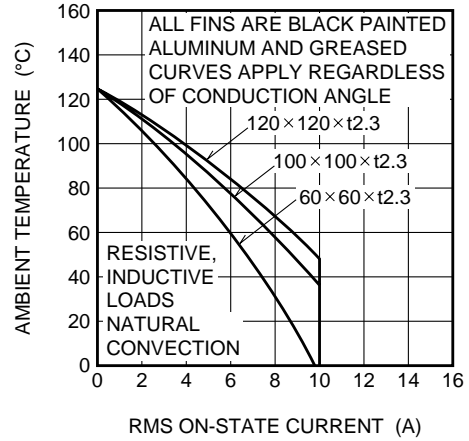
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MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

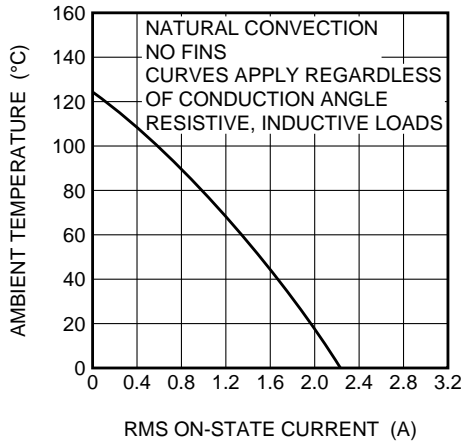
ALLOWABLE CASE TEMPERATURE VS. RMS ON-STATE CURRENT



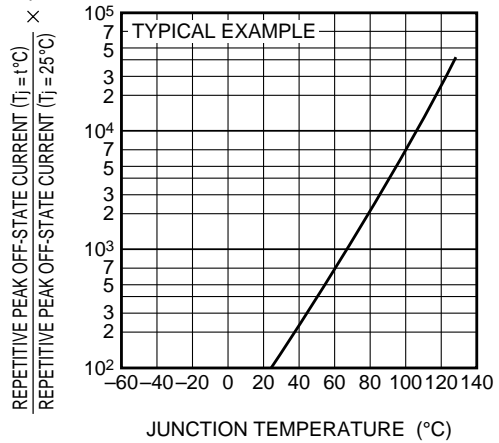
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



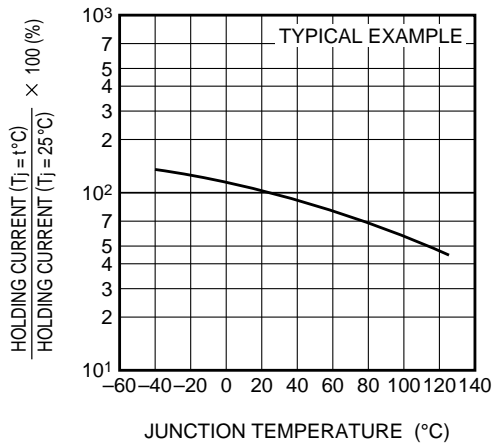
ALLOWABLE AMBIENT TEMPERATURE VS. RMS ON-STATE CURRENT



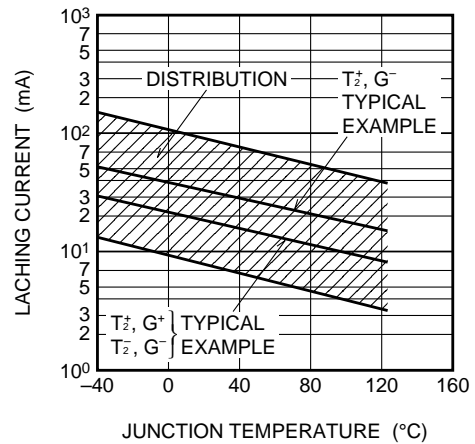
REPETITIVE PEAK OFF-STATE CURRENT VS. JUNCTION TEMPERATURE



HOLDING CURRENT VS. JUNCTION TEMPERATURE



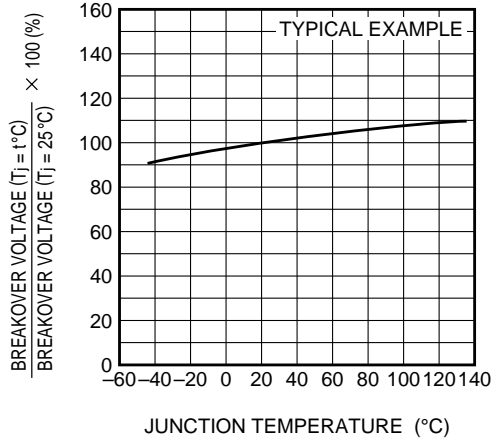
LACHING CURRENT VS. JUNCTION TEMPERATURE



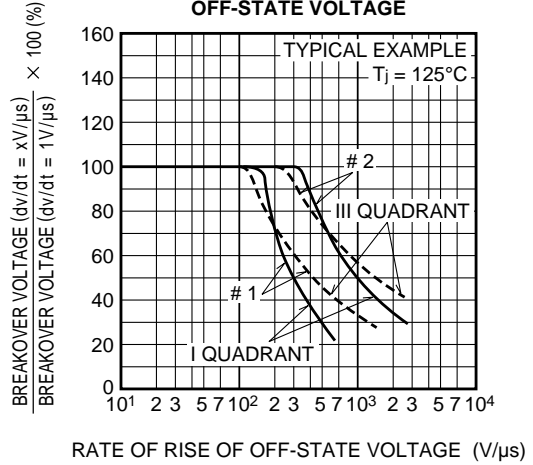
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MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

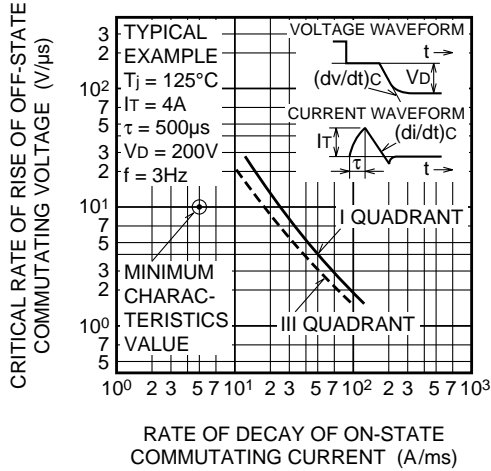
BREAKEOVER VOLTAGE VS. JUNCTION TEMPERATURE



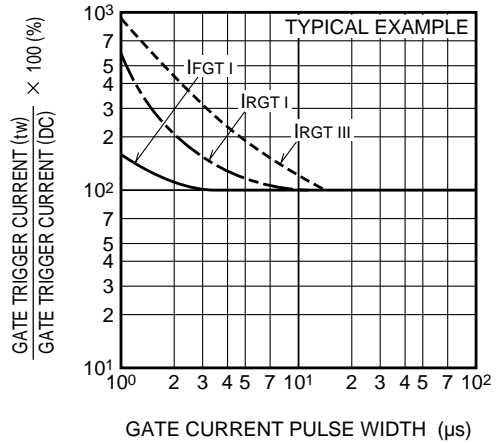
BREAKEOVER VOLTAGE VS. RATE OF RISE OF OFF-STATE VOLTAGE



COMMUTATION CHARACTERISTICS



GATE TRIGGER CURRENT VS. GATE CURRENT PULSE WIDTH



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

